

# TSM9434

# 20V P-Channel MOSFET



#### SOP-8

# 1

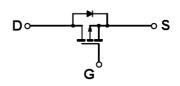
#### Pin Definition:

1. Source	8. Drair
2. Source	7. Drair
3. Source	<ol><li>Drain</li></ol>
4. Gate	<ol><li>Drain</li></ol>

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
	40 @ V <sub>GS</sub> = -4.5V	-6.4
-20	60 @ V <sub>GS</sub> = -2.5V	-5.1

## **Block Diagram**



P-Channel MOSFET

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

#### **Application**

- Load Switch
- PA Switch

#### **Ordering Information**

Part No.	Package	Packing		
TSM9434CS RL	SOP-8	2.5Kpcs / 13" Reel		
TSM9434CS RLG	SOP-8	2.5Kpcs / 13" Reel		

Note: "G" denotes Halogen Free Product.

**Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	-20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current		I <sub>D</sub>	-6.4	А	
Pulsed Drain Current		I <sub>DM</sub>	±10	А	
Continuous Source Current (Diode Conduction) <sup>a,b</sup>		I <sub>S</sub>	-2.5	А	
Maximum Power Dissipation	Ta = 25°C	P <sub>D</sub>	2.5	W	
	Ta = 70°C		1.6		
Operating Junction Temperature		T <sub>J</sub>	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ <sub>JC</sub>	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

#### Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



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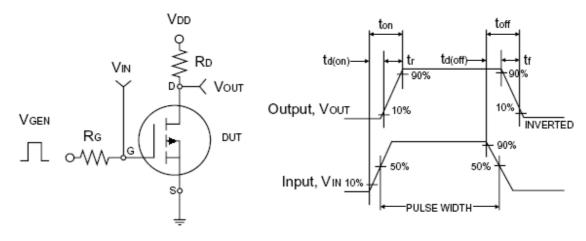


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250uA$	V <sub>GS(TH)</sub>	-0.4		-1.0	V
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	uA
Gate Body Leakage	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
On-State Drain Current	$V_{DS} \le -5V, V_{GS} = -4.5V$	I <sub>D(ON)</sub>	-10			Α
	$V_{GS} = -4.5V$ , $I_{D} = -6.4A$	_		31	40	mΩ
Drain-Source On-State Resistance	Orain-Source On-State Resistance $V_{GS} = -2.5V, I_D = -5.1A$ $R_{DS(ON)}$	K <sub>DS(ON)</sub>		45	60	
Forward Transconductance	$V_{DS} = -9V, I_{D} = -6.4A$	<b>g</b> fs		14		S
Diode Forward Voltage	$I_S = -2.5A, V_{GS} = 0V$	V <sub>SD</sub>		- 0.9	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge		$Q_g$		12.5	19	
Gate-Source Charge	$V_{DS} = -10V, I_{D} = -6.4A,$ $V_{GS} = -4.5V$	$Q_{gs}$		1.7		nC
Gate-Drain Charge		$Q_gd$		3.3		]
Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>iss</sub>		1020		
Output Capacitance		C <sub>oss</sub>		191		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		140		
Switching <sup>C</sup>						
Turn-On Delay Time	$V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t <sub>d(on)</sub>		25	40	
Turn-On Rise Time		t <sub>r</sub>		43	65	0
Turn-Off Delay Time		t <sub>d(off)</sub>		71	110	nS
Turn-Off Fall Time		t <sub>f</sub>		48	75	

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

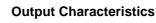
Switchin Waveforms

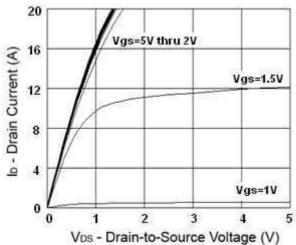




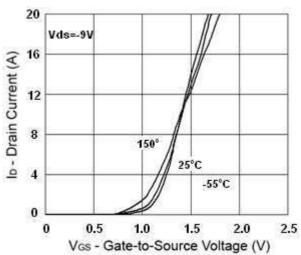


#### **Electrical Characteristics Curve** (Ta = 25 °C, unless otherwise noted)

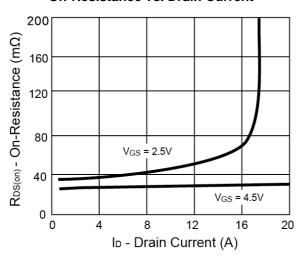




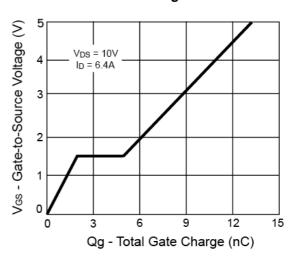
# **Transfer Characteristics**



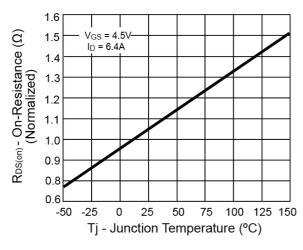
#### **On-Resistance vs. Drain Current**



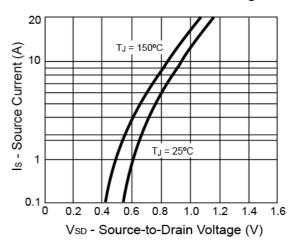
**Gate Charge** 



#### On-Resistance vs. Junction Temperature



#### **Source-Drain Diode Forward Voltage**

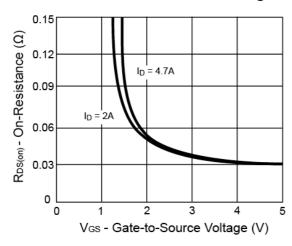




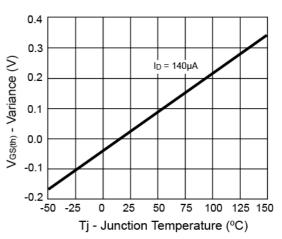


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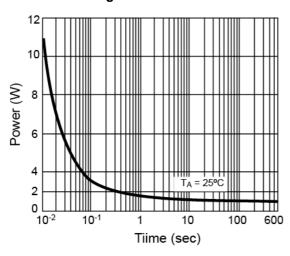
#### On-Resistance vs. Gate-Source Voltage



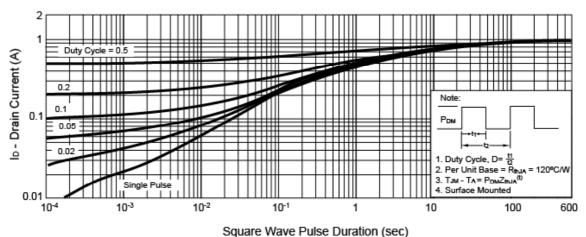
#### **Threshold Voltage**



#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



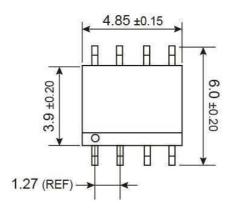
4/6

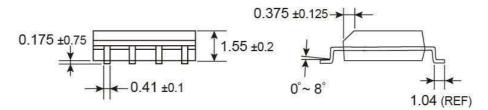
Version: B12





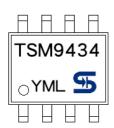
# **SOP-8 Mechanical Drawing**





Unit: Millimeters

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

= Month Code for Halogen Free Product

5/6

(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

Version: B12



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